

Search Notes

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	16	hard adj mask and hydroflouric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 06:33
L2	13	hard adj mask and hydroflouric adj acid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 06:33
L3	13	hard adj mask and hydroflouric adj acid and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 06:35
L4	3	hard adj mask same hydroflouric adj acid and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 06:41
L5	377	hard adj mask same hf same etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 06:41
L6	60	hard adj mask same hf with acid same etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 06:42
L7	12	hard adj mask with hf with acid same etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 06:42
L10	0	hard adj mask with oxynitride same ion adj implant\$6 same etch with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:10
L11	431	hard adj mask with oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:10

L12	28	hard adj mask with oxynitride same etch\$3 with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:11
L13	1	hard adj mask with oxynitride same etch\$3 with rate same implant\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:11
L14	28	hard adj mask with oxynitride same etch\$3 with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:16
L15	0	hard adj mask with sion same etch\$3 with rate same implant\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:13
L16	19	hard adj mask with sion same etch\$3 with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:13
L17	1	hard adj mask with sion same etch\$3 with rate same ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:14
L18	2	hard adj mask with sion and etch\$3 with rate same implant\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:14
L19	5	hard adj mask with oxynitride and etch\$3 with rate same implant\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:32
L20	1727	438/745	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:33
L21	557	438/705	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:34

L22	708	438/756	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:34
S1	44	hard adj mask with silicon adj oxide same ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 06:33
S2	43	hard adj mask with silicon adj dioxide same ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:42
S3	86	hard adj mask with silicon adj (dioxide or oxide) same ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:43
S4	24	hard adj mask with silicon adj (dioxide or oxide) same ion adj implant\$6 and etch near rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:43
S5	31	hard adj mask with silicon adj (dioxide or oxide) same ion adj implant\$6 and etch\$3 near rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:45
S6	5	hard adj mask with silicon adj (dioxide or oxide) same ion adj implant\$6 and etch\$3 near rate and thermal with silicon adj (dioxide or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:53
S7	2	hard adj mask with silicon adj (dioxide or oxide) same ion adj implant\$6 same etch\$3 near rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:56
S8	182	silicon adj (dioxide or oxide) same ion adj implant\$6 same etch\$3 near rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:53
S9	2	hard adj mask with silicon adj (dioxide or oxide) same ion adj implant\$6 same etch\$3 with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:56

S10	86	hard adj mask with silicon adj (dioxide or oxide) same ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:57
S11	165	hard adj mask same silicon adj (dioxide or oxide) same ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:57
S12	23	hard adj mask same silicon adj (dioxide or oxide) same ion adj implant\$6 same thermal with silicon adj (dioxide or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:31
S13	7	hard adj mask same silicon adj (dioxide or oxide) with ion adj implant\$6 same thermal with silicon adj (dioxide or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 16:58
S14	7	hard adj mask same silicon adj (dioxide or oxide or oxy nitride) with ion adj implant\$6 same thermal with silicon adj (dioxide or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:26
S15	1	hard adj mask with low adj temperature near silicon adj (dioxide or oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:33
S16	17	hard adj mask with low adj temperature adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:41
S17	33	ion adj implant\$6 with low adj temperature adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:44
S18	2	ion adj implant\$6 with low adj temperature adj oxide same damage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:42
S19	0	ion adj implant\$6 with low adj temperature adj oxide same hard adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:44

S20	4	ion adj implant\$6 with low adj temperature adj oxide and etch adj rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:47
S21	531	(438/738).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/28 17:48
S22	106	S21 and ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 17:50
S23	1	S21 and ion adj implant\$6 and Ito	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:01
S24	8	"6207517"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:23
S25	0	"6207517" and oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:24
S26	430	hard adj mask with oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:24
S27	2	hard adj mask with oxynitride with ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:31
S28	10	hard adj mask with oxynitride and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:26
S29	2	hard adj mask with oxynitride and S21 and ion adj implant\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:27

S30	3	hard adj mask same oxynitride same ion adj implant\$6 same etch with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 07:10
S31	9	oxynitride same ion adj implant\$6 same etch with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:36
S32	25	oxynitride with ion adj implant\$6 and etch with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:36
S33	43	mask with oxynitride same ion adj implantation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:43
S34	25	mask with oxynitride with ion adj implantation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:43
S35	13	mask with silicon adj oxynitride with ion adj implantation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:43
S36	1	mask with silicon adj oxynitride with ion adj implantation and etch\$3 with rate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 18:44